SiZ700DT

Vishay Siliconix

N-Channel 20-V (D-S) MOSFETs

PRODUCT SUMMARY				
	V_{DS} (V)	$R_{DS(on)}$ (Ω)	I_D (A)	Q_g (Typ.)
Channel-1	20	0.0086 at V_{GS} = 10 V	16[a]	9.5 nC
		0.0108 at V_{GS} = 4.5 V	16[a]	
Channel-2	20	0.0058 at V_{GS} = 10 V	16[a]	27 nC
		0.0066 at V_{GS} = 4.5 V	16[a]	

FEATURES

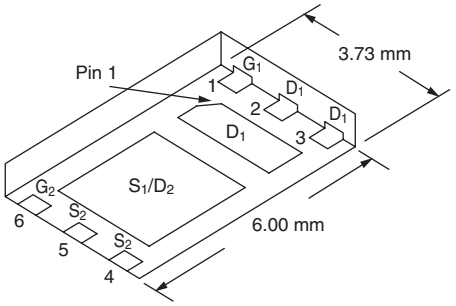
- **Halogen-free According to IEC 61249-2-21 Definition**
- TrenchFET® Power MOSFETs
- 100 % R_g Tested
- Compliant to RoHS Directive 2002/95/EC

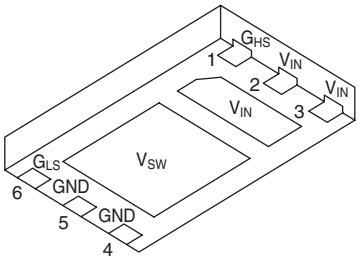
Pb-free
RoHS COMPLIANT
HALOGEN FREE

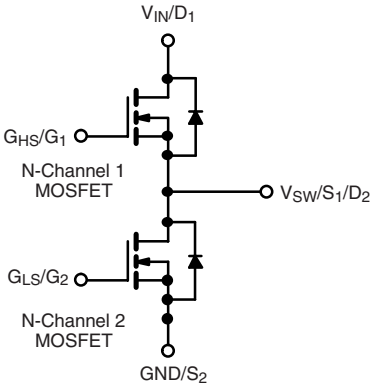
APPLICATIONS

- Notebook System Power

PowerPAIR™ 6 x 3.7







Ordering Information: SiZ700DT-T1-GE3 (Lead (Pb)-free and Halogen-free)

ABSOLUTE MAXIMUM RATINGS T_A = 25 °C, unless otherwise noted					
Parameter		**Symbol**	**Channel-1**	**Channel-2**	**Unit**
Drain-Source Voltage		V_{DS}	20	20	V
Gate-Source Voltage		V_{GS}	± 16		
Continuous Drain Current (T_J = 150 °C)	T_C = 25 °C	I_D	16[a]	16[a]	A
	T_C = 70 °C		16[a]	16[a]	
	T_A = 25 °C		13.1[b, c]	17.3[b, c]	
	T_A = 70 °C		10.5[b, c]	13.9[b, c]	
Pulsed Drain Current		I_{DM}	60	60	
Source Drain Current Diode Current	T_C = 25 °C	I_S	14.7	16[a]	
	T_A = 25 °C		1.96[b, c]	2.3[b, c]	
Maximum Power Dissipation	T_C = 25 °C	P_D	2.36	2.8	W
	T_C = 70 °C		1.5	1.78	
	T_A = 25 °C		1.4[b, c]	1.47[b, c]	
	T_A = 70 °C		0.9[b, c]	0.94[b, c]	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	- 55 to 150		°C
Soldering Recommendations (Peak Temperature)[d, e]			260		

THERMAL RESISTANCE RATINGS							
			Channel-1		**Channel-2**		
Parameter		**Symbol**	**Typ.**	**Max.**	**Typ.**	**Max.**	**Unit**
Maximum Junction-to-Ambient[b, f]	t ≤ 10 s	R_{thJA}	39	53	33	45	°C/W
Maximum Junction-to-Case (Drain)	Steady State	R_{thJC}	5.7	7.1	3.7	4.6	

Notes:
a. Package limited.
b. Surface Mounted on 1" x 1" FR4 board.
c. t = 10 s.
d. See Solder Profile (www.vishay.com/ppg?73257). The PowerPAIR is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.
e. Rework Conditions: manual soldering with a soldering iron is not recommended for leadless components.
f. Maximum under Steady State conditions is 90 °C/W for Channel-1 and 85 °C/W for Channel-2.

SPECIFICATIONS T_J = 25 °C, unless otherwise noted							
Parameter	**Symbol**	**Test Conditions**		**Min.**	**Typ.**	**Max.**	**Unit**
Static							
Drain-Source Breakdown Voltage	V_{DS}	V_{GS} = 0 V, I_D = 250 µA	Ch-1	20			V
		V_{GS} = 0 V, I_D = 250 µA	Ch-2	20			
V_{DS} Temperature Coefficient	$\Delta V_{DS}/T_J$	I_D = 250 µA	Ch-1		21		mV/°C
		I_D = 250 µA	Ch-2		21		
$V_{GS(th)}$ Temperature Coefficient	$\Delta V_{GS(th)}/T_J$	I_D = 250 µA	Ch-1		- 5.8		
		I_D = 250 µA	Ch-2		- 5.8		
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250 µA	Ch-1	0.8		2.2	V
		V_{DS} = V_{GS}, I_D = 250 µA	Ch-2	0.8		2.2	
Gate-Body Leakage	I_{GSS}	V_{DS} = 0 V, V_{GS} = ± 16 V	Ch-1			± 100	nA
			Ch-2			± 100	
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = 20 V, V_{GS} = 0 V	Ch-1			1	µA
		V_{DS} = 20 V, V_{GS} = 0 V	Ch-2			1	
		V_{DS} = 20 V, V_{GS} = 0 V, T_J = 55 °C	Ch-1			10	
		V_{DS} = 20 V, V_{GS} = 0 V, T_J = 55 °C	Ch-2			10	
On-State Drain Current[b]	$I_{D(on)}$	$V_{DS} \geq$ 5 V, V_{GS} = 10 V	Ch-1	30			A
		$V_{DS} \geq$ 5 V, V_{GS} = 10 V	Ch-2	30			
Drain-Source On-State Resistance[b]	$R_{DS(on)}$	V_{GS} = 10 V, I_D = 15 A	Ch-1		0.007	0.0086	Ω
		V_{GS} = 10 V, I_D = 20 A	Ch-2		0.0047	0.0058	
		V_{GS} = 4.5 V, I_D = 10 A	Ch-1		0.0088	0.0108	
		V_{GS} = 4.5 V, I_D = 15 A	Ch-2		0.0054	0.0066	
Forward Transconductance[b]	g_{fs}	V_{DS} = 10 V, I_D = 15 A	Ch-1		60		S
		V_{DS} = 10 V, I_D = 20 A	Ch-2		100		
Dynamic[a]							
Input Capacitance	C_{iss}	Channel-1 V_{DS} = 10 V, V_{GS} = 0 V, f = 1 MHz	Ch-1		1300		pF
			Ch-2		3860		
Output Capacitance	C_{oss}		Ch-1		290		
		Channel-2 V_{DS} = 10 V, V_{GS} = 0 V, f = 1 MHz	Ch-2		760		
Reverse Transfer Capacitance	C_{rss}		Ch-1		132		
			Ch-2		350		
Total Gate Charge	Q_g	V_{DS} = 10 V, V_{GS} = 10 V, I_D = 15 A	Ch-1		20	35	nC
		V_{DS} = 10 V, V_{GS} = 10 V, I_D = 20 A	Ch-2		55	85	
		Channel-1 V_{DS} = 10 V, V_{GS} = 4.5 V, I_D = 15 A	Ch-1		9.5	15	
			Ch-2		27	45	
Gate-Source Charge	Q_{gs}		Ch-1		3.2		
		Channel-2 V_{DS} = 10 V, V_{GS} = 4.5 V, I_D = 20 A	Ch-2		9.2		
Gate-Drain Charge	Q_{gd}		Ch-1		2.4		
			Ch-2		7.1		
Gate Resistance	R_g	f = 1 MHz	Ch-1	0.3	1.3	2.6	Ω
			Ch-2	0.2	1.0	2.0	

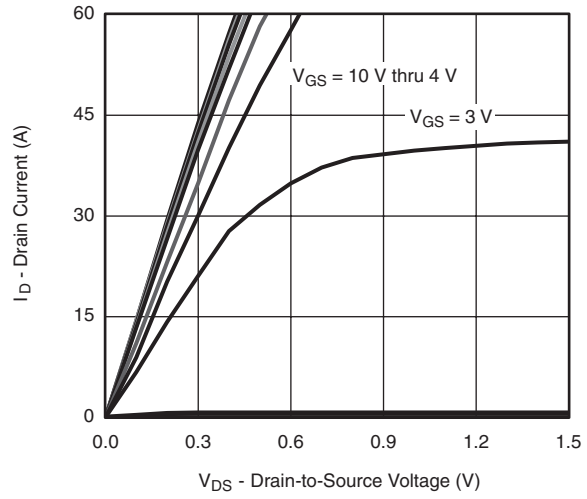
Notes:
a. Guaranteed by design, not subject to production testing.
b. Pulse test; pulse width ≤ 300 µs, duty cycle ≤ 2 %.

SPECIFICATIONS T_J = 25 °C, unless otherwise noted							
Parameter	**Symbol**	**Test Conditions**		**Min.**	**Typ.**	**Max.**	**Unit**
Dynamic[a]							
Turn-On Delay Time	$t_{d(on)}$	Channel-1 V_{DD} = 10 V, R_L = 10 Ω $I_D \cong$ 1.0 A, V_{GEN} = 4.5 V, R_g = 1 Ω	Ch-1		9	15	ns
			Ch-2		13	20	
Rise Time	t_r		Ch-1		8	15	
			Ch-2		8	15	
Turn-Off Delay Time	$t_{d(off)}$	Channel-2 V_{DD} = 10 V, R_L = 10 Ω $I_D \cong$ 1.0 A, V_{GEN} = 4.5 V, R_g = 1 Ω	Ch-1		25	40	
			Ch-2		52	80	
Fall Time	t_f		Ch-1		8	15	
			Ch-2		15	25	
Turn-On Delay Time	$t_{d(on)}$	Channel-1 V_{DD} = 10 V, R_L = 10 Ω $I_D \cong$ 1.0 A, V_{GEN} = 10 V, R_g = 1 Ω	Ch-1		8	15	
			Ch-2		12	20	
Rise Time	t_r		Ch-1		9	15	
			Ch-2		8	15	
Turn-Off Delay Time	$t_{d(off)}$	Channel-2 V_{DD} = 10 V, R_L = 10 Ω $I_D \cong$ 1.0 A, V_{GEN} = 10 V, R_g = 1 Ω	Ch-1		25	40	
			Ch-2		47	75	
Fall Time	t_f		Ch-1		8	15	
			Ch-2		10	15	
Drain-Source Body Diode Characteristics							
Continuous Source-Drain Diode Current	I_S	T_C = 25 °C	Ch-1			14.7	A
			Ch-2			16	
Pulse Diode Forward Current[a]	I_{SM}		Ch-1			60	
			Ch-2			60	
Body Diode Voltage	V_{SD}	I_S = 2.0 A, V_{GS} = 0 V	Ch-1		0.8	1.2	V
		I_S = 2.3 A, V_{GS} = 0 V	Ch-2		0.8	1.2	
Body Diode Reverse Recovery Time	t_{rr}	Channel-1 I_F = 2.0 A, dI/dt = 100 A/µs, T_J = 25 °C Channel-2 I_F = 2.3 A, dI/dt = 100 A/µs, T_J = 25 °C	Ch-1		25	50	ns
			Ch-2		40	80	
Body Diode Reverse Recovery Charge	Q_{rr}		Ch-1		13	25	nC
			Ch-2		31	60	
Reverse Recovery Fall Time	t_a		Ch-1		12		ns
			Ch-2		21		
Reverse Recovery Rise Time	t_b		Ch-1		13		
			Ch-2		19		

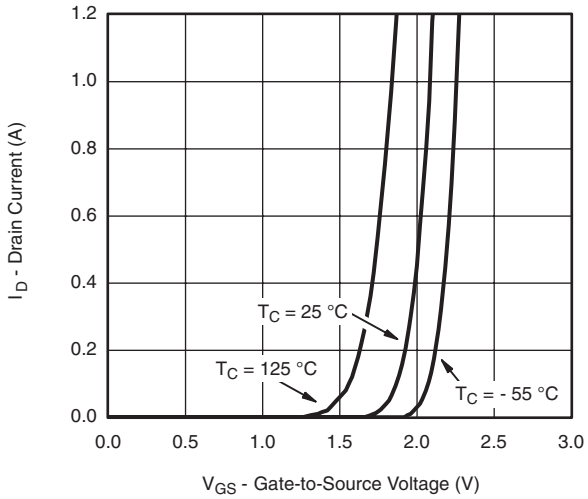
Notes:
a. Guaranteed by design, not subject to production testing.
b. Pulse test; pulse width ≤ 300 µs, duty cycle ≤ 2 %.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

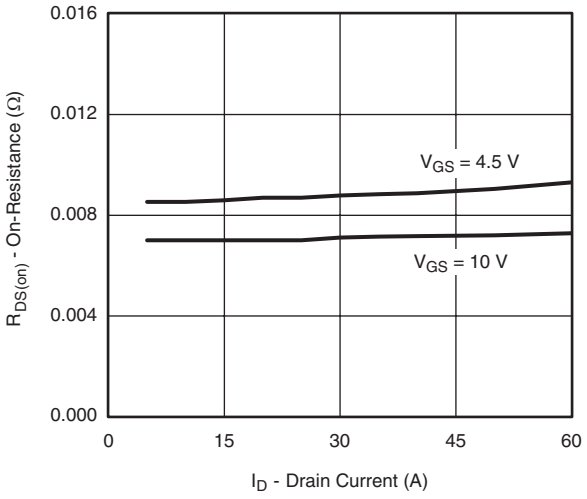
CHANNEL-1 TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



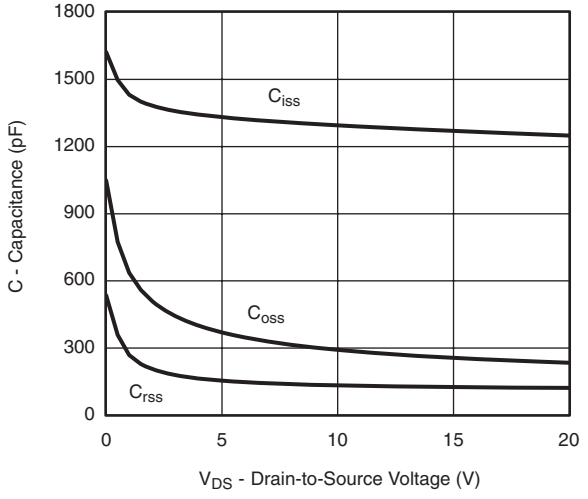
Output Characteristics



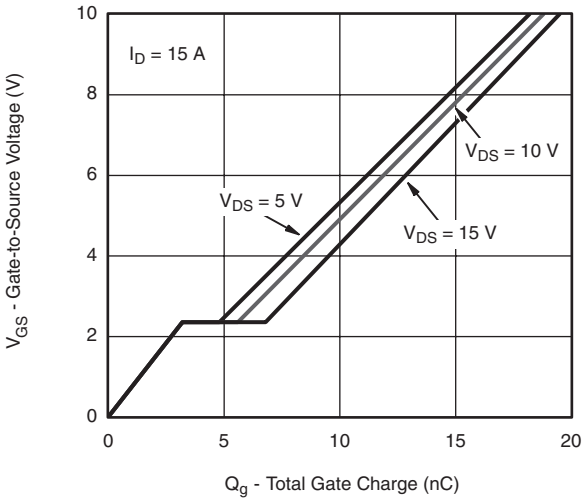
Transfer Characteristics



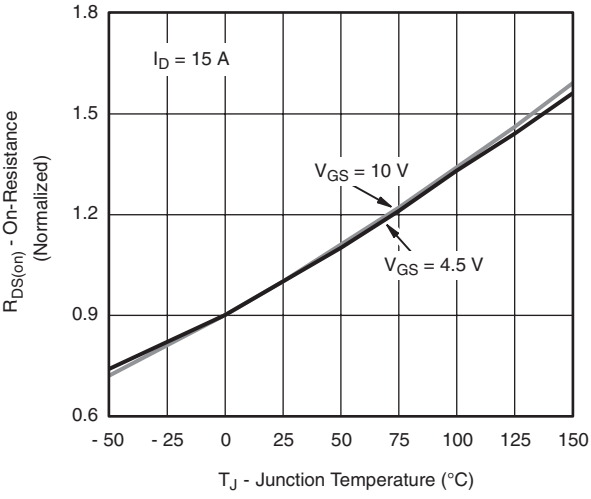
On-Resistance vs. Drain Current



Capacitance

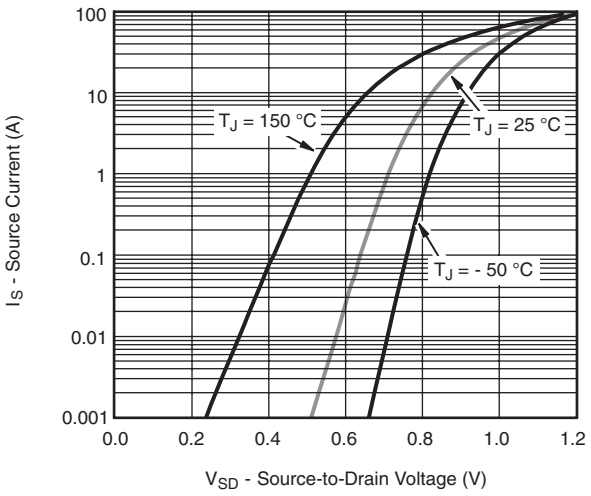


Gate Charge

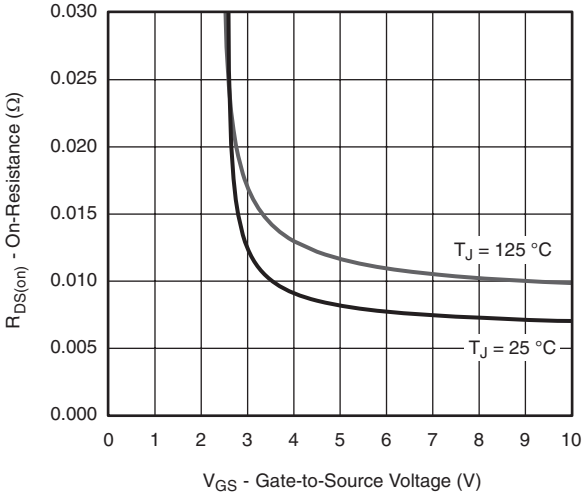


On-Resistance vs. Junction Temperature

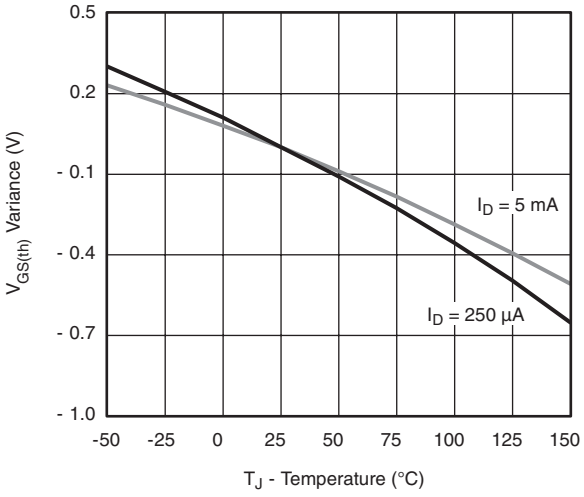
CHANNEL-1 TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



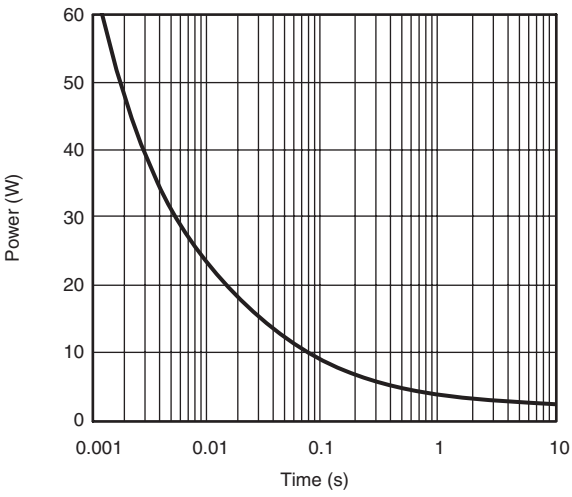
Source-Drain Diode Forward Voltage



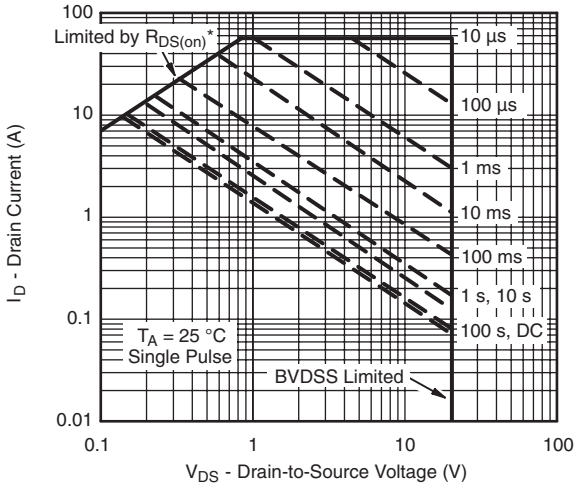
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage



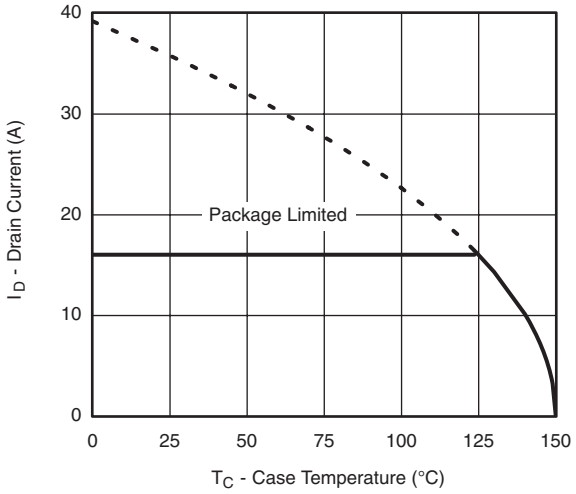
Single Pulse Power



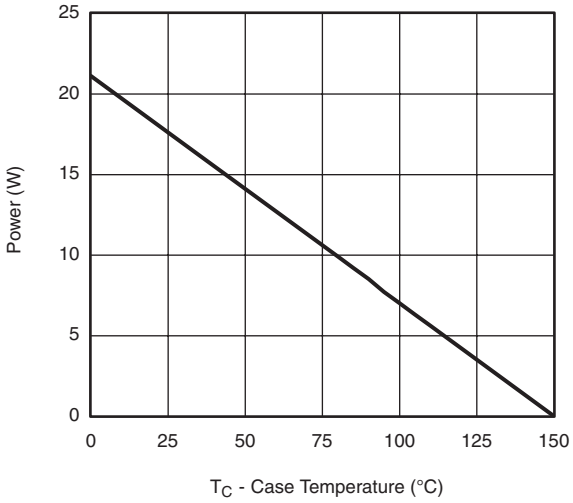
* V_{GS} > minimum V_{GS} at which $R_{DS(on)}$ is specified

Safe Operating Area, Junction-to-Ambient

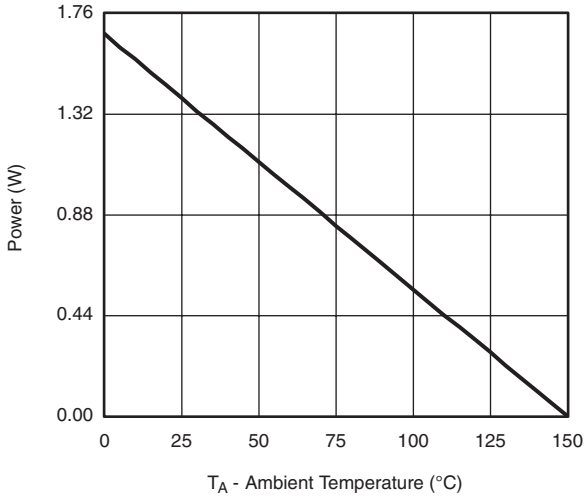
CHANNEL-1 TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Current Derating*



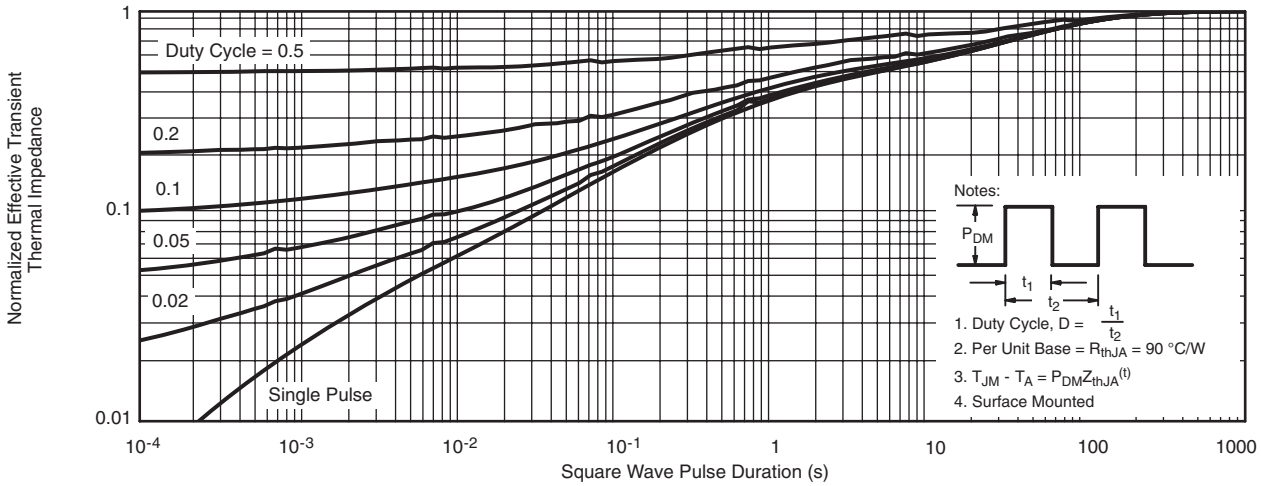
Power, Junction-to-Case



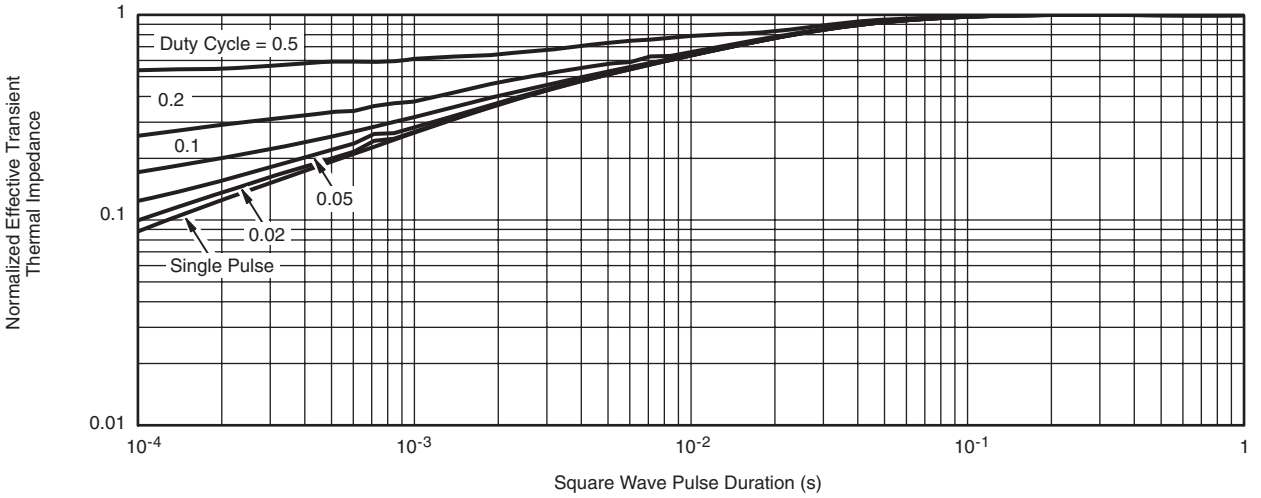
Power, Junction-to-Ambient

* The power dissipation P_D is based on $T_{J(max)}$ = 150 °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

CHANNEL-1 TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

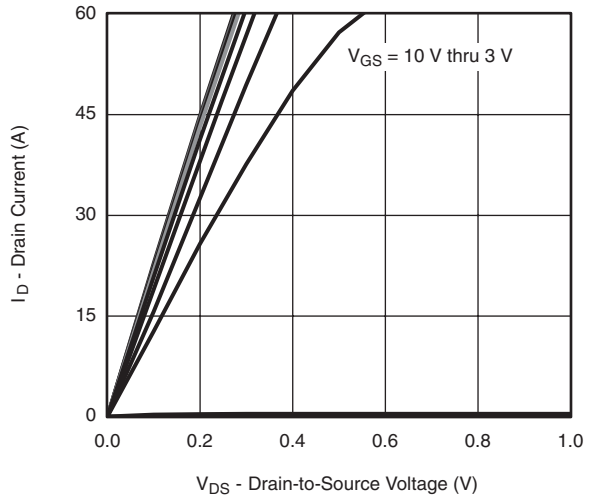


Normalized Thermal Transient Impedance, Junction-to-Ambient

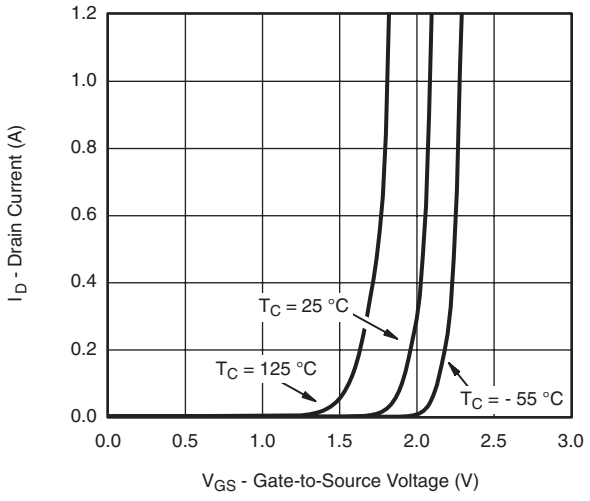


Normalized Thermal Transient Impedance, Junction-to-Case

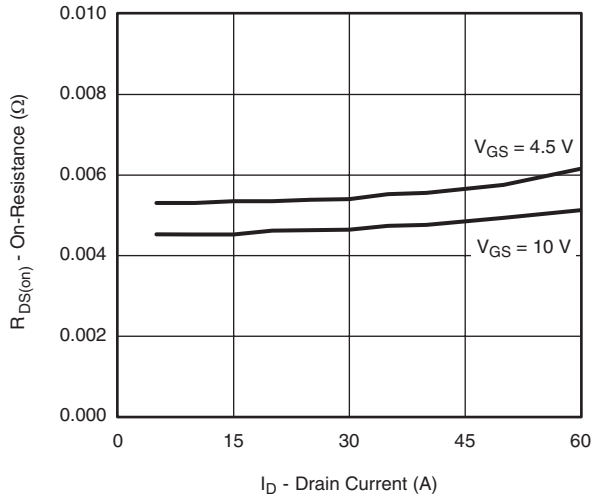
CHANNEL-2 TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



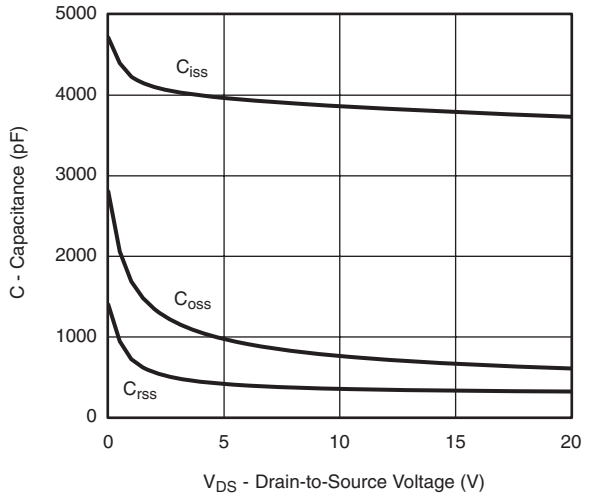
Output Characteristics



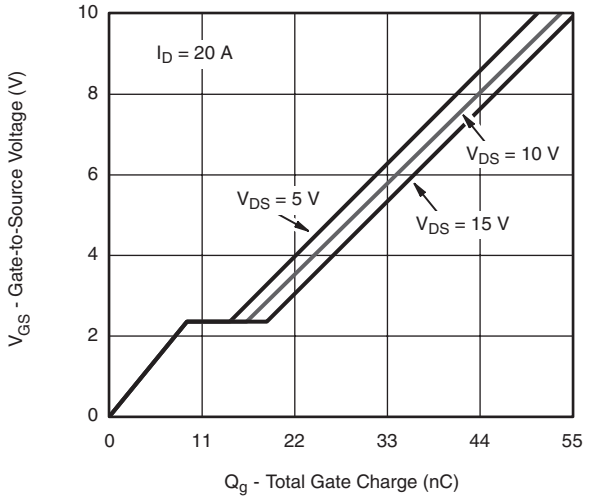
Transfer Characteristics



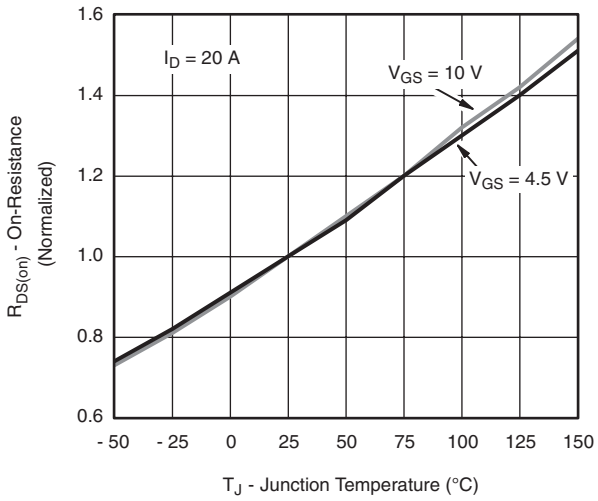
On-Resistance vs. Drain Current



Capacitance

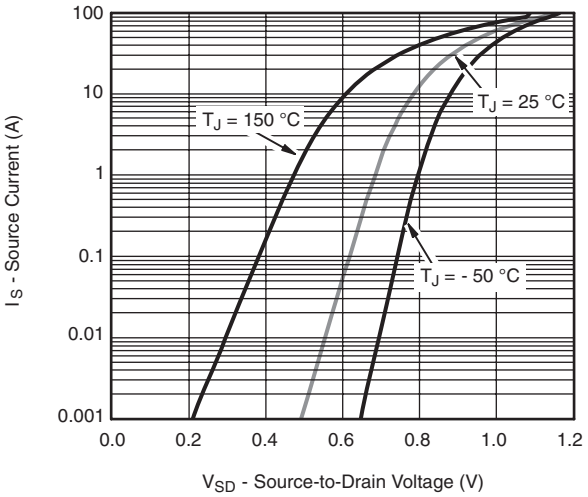


Gate Charge

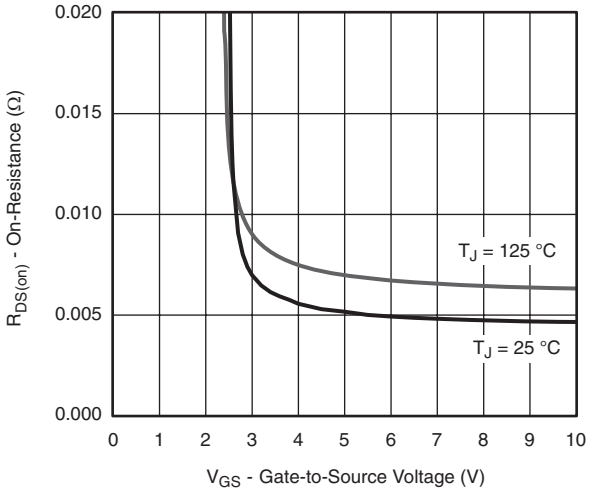


On-Resistance vs. Junction Temperature

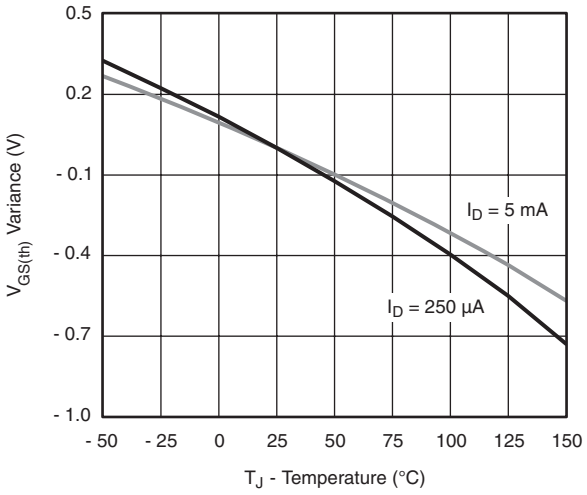
CHANNEL-2 TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



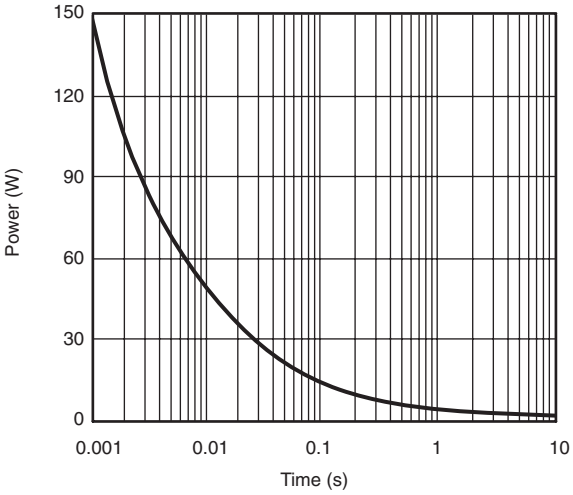
Source-Drain Diode Forward Voltage



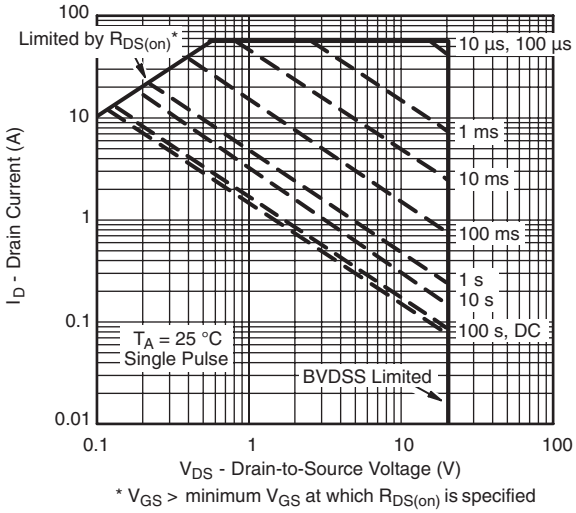
On-Resistance vs. Gate-to-Source



Threshold Voltage



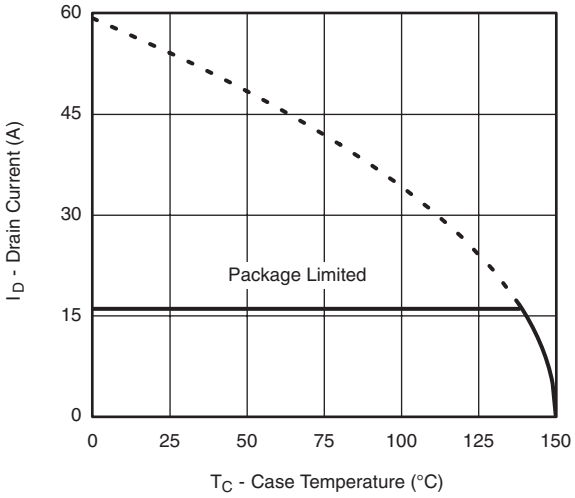
Single Pulse Power



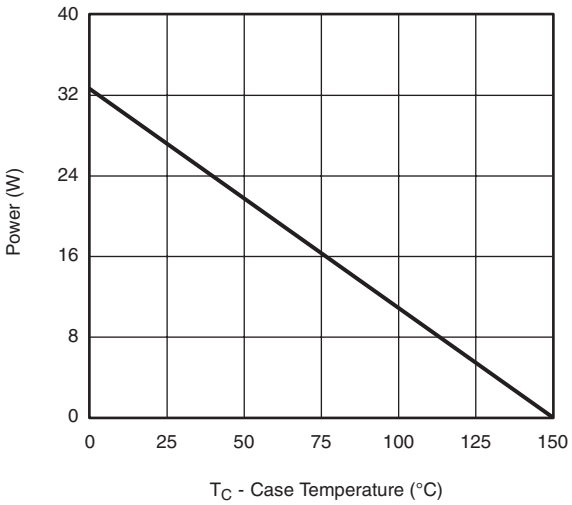
* V_{GS} > minimum V_{GS} at which $R_{DS(on)}$ is specified

Safe Operating Area, Junction-to-Ambient

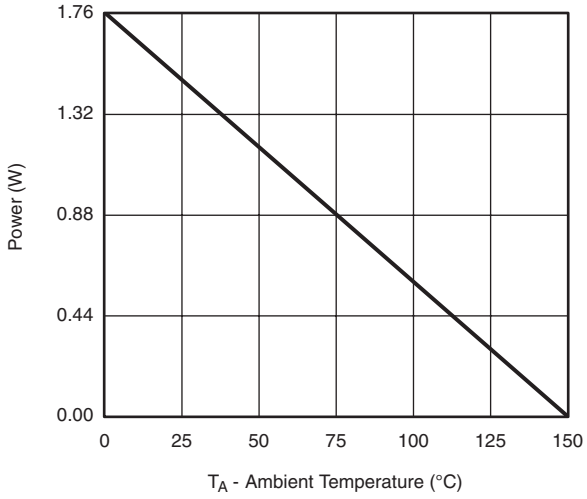
CHANNEL-2 TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Current Derating*



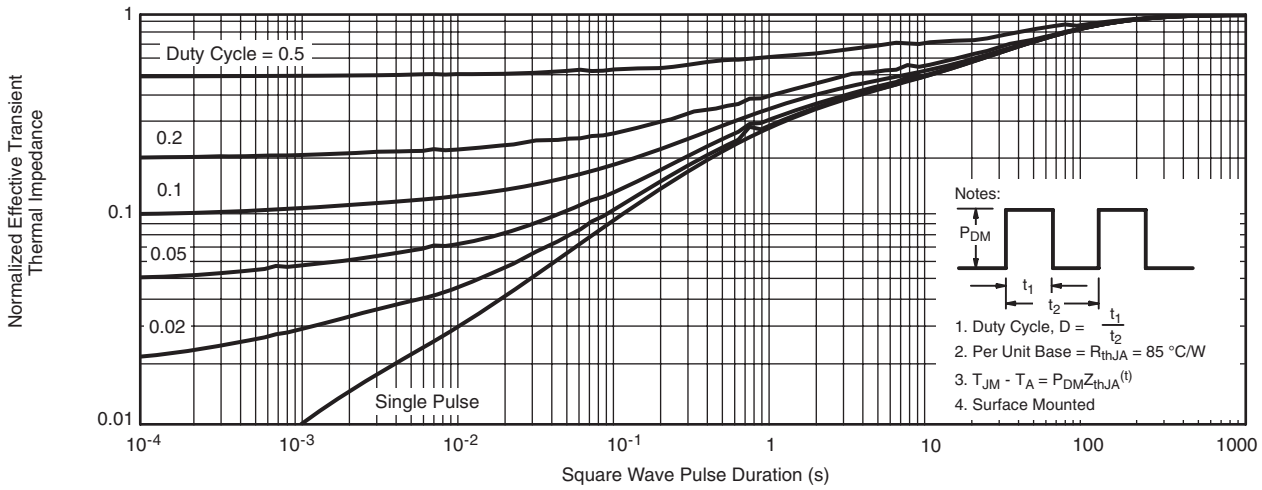
Power, Junction-to-Case



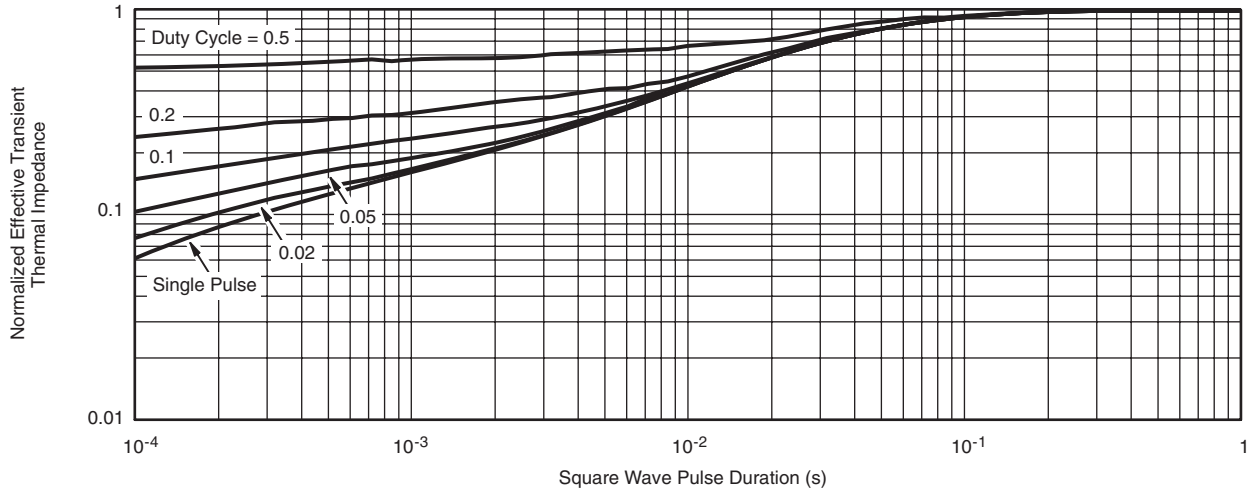
Power, Junction-to-Ambient

* The power dissipation P_D is based on $T_{J(max)}$ = 150 °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

CHANNEL-2 TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Case

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